"REDUCING CONSUMER ELECTRONICS' IMPACTS WITH GALLIUM NITRIDE (GAN) POWER SEMICONDUCTORS"



October 28, 2021 1:00 pm EDT (will start promptly)

Presenters:

Anthony Schiro

VP of Quality & Sustainability Navitas Semiconductor

Dr. Caroline Taylor, Chief Scientist EarthShift Global





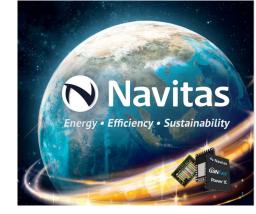


REDUCING CONSUMER ELECTRONICS' IMPACTS WITH GALLIUM NITRIDE (GaN) POWER SEMICONDUCTORS

COMPARISON OF LIFE CYCLE IMPACTS FOR CONSUMER CHARGING USING GaN TECHNOLOGY IN PLACE OF SI CHARGERS.

28 OCTOBER 2021

CAROLINE TAYLOR, PHD, CAROLINE@EARTHSHIFTGLOBAL.COM ANTHONY SCHIRO, ANTHONY.SCHIRO@NAVITASSEMI.COM www.earthshiftglobal.com © 2021 EarthShift Global LLC – All Rights Reserved



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WHAT IS A POWER SEMICONDUCTOR?



Microprocessor



Power Semiconductor



Consumes power through processing data / information Converts power from one form to another based on end use requirement

WHAT IS A POWER SEMICONDUCTOR?



Power Semiconductor



Converts power from one form to another based on end use requirement <image><section-header><section-header><section-header><section-header><section-header>

Solar

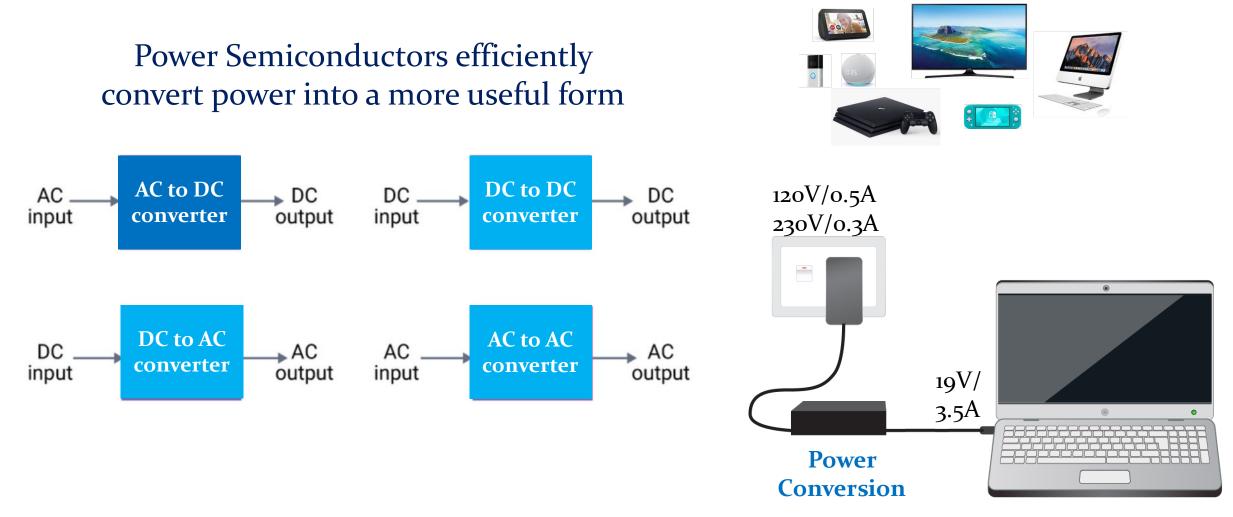




WHAT IS A POWER SEMICONDUCTOR?



Consumer/Mobile

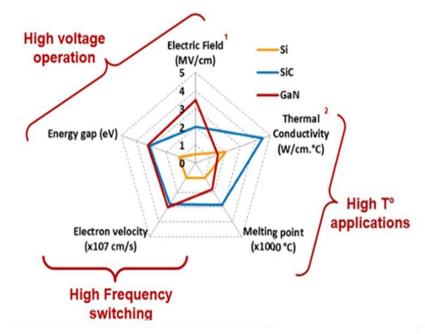




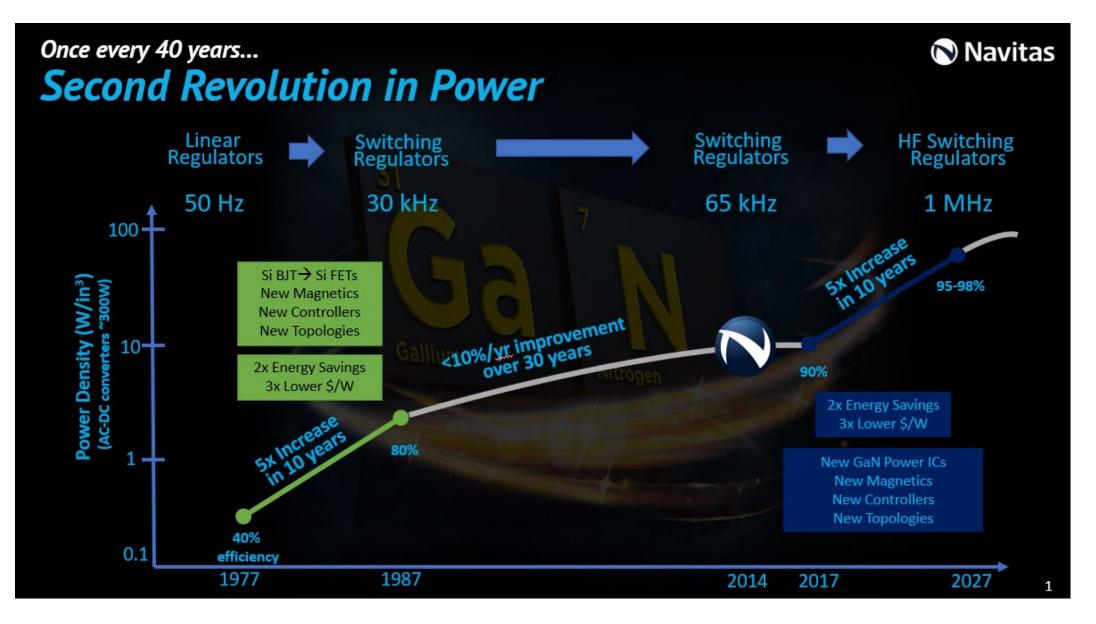


- New semiconductor material
 - "Silicon chip" → "GaN Chip"
- 20x faster
- 5x smaller
- 2x more efficient

Speed & efficiency translate to more power, faster charging in smaller size & weight









65W AC/DC adapter 80-90% efficiency = 6.5-13W wasted



65W AC/DC adapter 93% efficiency = 4.5W wasted

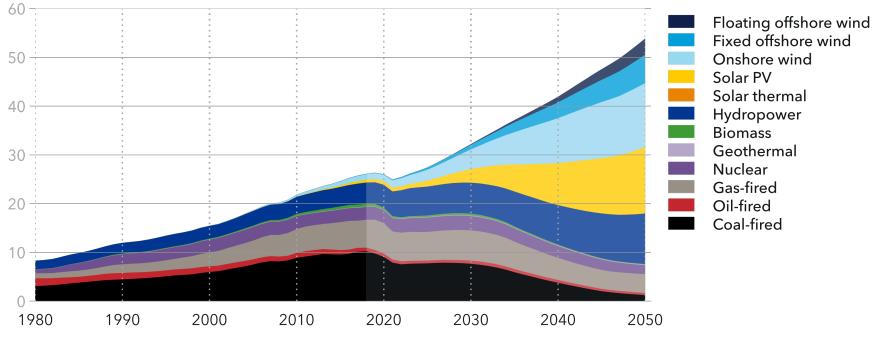




Fossil Fuel → Electric = increased impact of efficient electricity conversion

World electricity generation by power station type

Units: PWh/yr

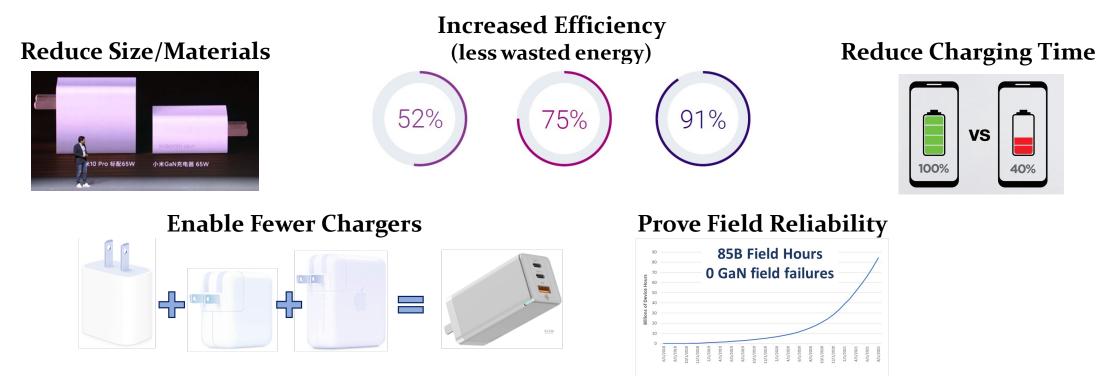


Historical data source: IEA WEB (2018), IRENA (2019)

INITIAL DESIGN FOCUS – MOBILE CHARGERS



• Implement GaN Technology in the mobile charging market to:



• With so much material and energy savings – how do we quantify the Sustainability benefits of GaN?

STUDY GOAL & SCOPE

- Assess the potential life cycle environmental benefits of GaN power semiconductors in place of conventional Si;
- Confirm alignment of life cycle impacts with product intent; and
- Understand potential hotspots and design factors.

Functional Units I & II: 1 wafer, 1 die

 Production of GaN and Si power semiconductor wafers (6", 8", respectively) and dies

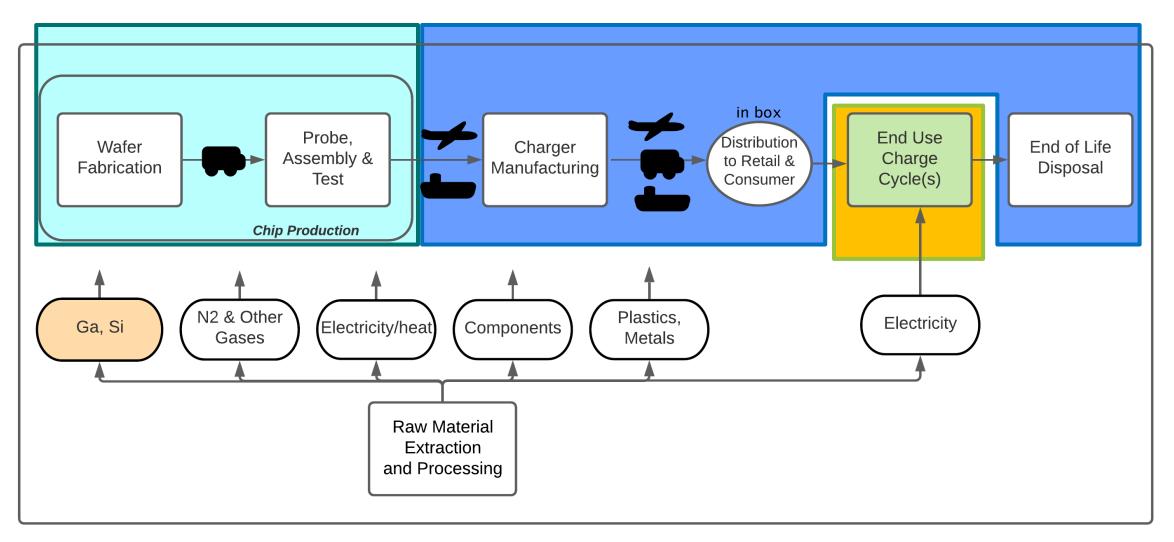
Functional Unit III: "charging a laptop over charger life"

 Provision of charging service in the US & China –with 65W GaN-based and Si-based chargers





SYSTEM BOUNDARY

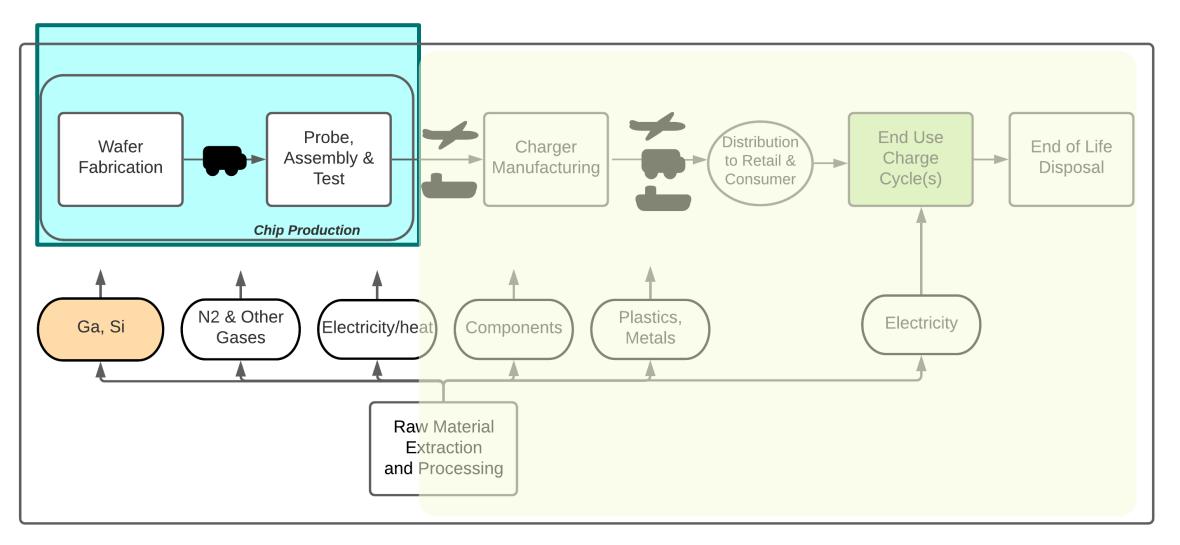




TECHNICAL DETAILS

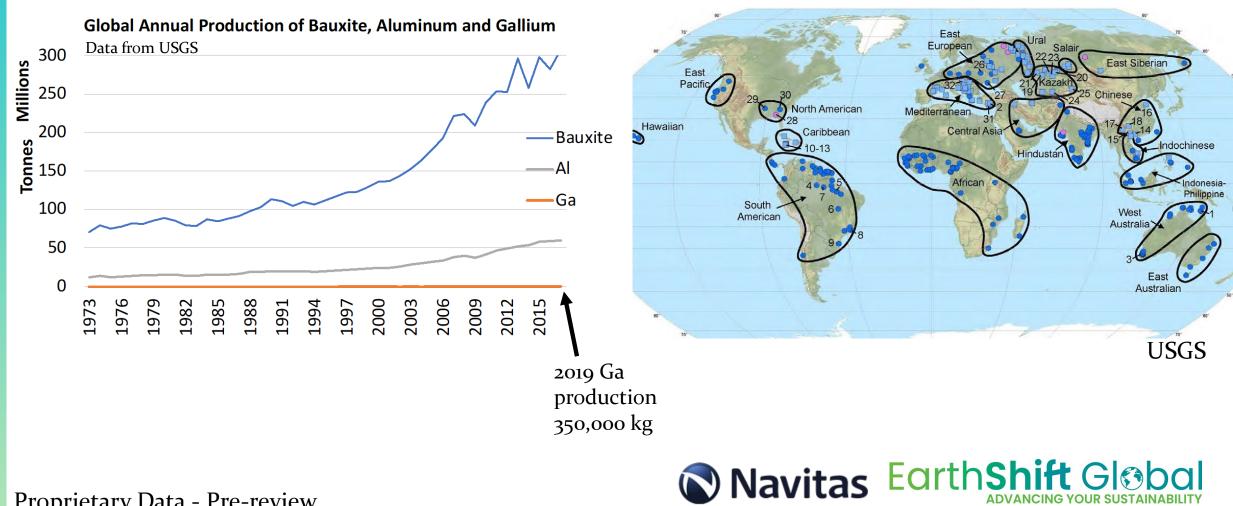
Inventory	
Primary data	Test data (energy use & efficiency, including standby or parasitic energy consumption), product teardowns, BoM data Primary component fabrication: literature, expert input
Background data	Secondary components – library data (ecoinvent 3.7, GaBi electronics extensions 2021) ecoinvent 3.7, Market and literature values, expert consultation
Geography & Logistics	
Manufacturing	Fabrication (wafer, die) - Taiwan, Grid electricity Chargers – Guandong, China, Grid electricity
US Use	West Coast US, WECC Grid or Household solar Via air from Taiwan, sensitivity for ocean transport
Chinese Use	Guangdong Province, Chinese Grid or Household solar Via air from Taiwan, sensitivity for ocean transport
Use/Operating	
Charger life (default)	3 years (used 50 weeks/year, 5 days/week for 3 years, charger unplugged rest of time)
Usage scenarios	Business travel, business office, business+home office, home use
Impact Model(s) & Tools	
IAMs	IPCC 2013 100y; ReCiPe 2016 Endpoint H/A; AWARE; CED
Tool(s) Proprietary Data - Pre-rev	SimaPro 9.1.1 view

POWER SEMICONDUCTOR PRODUCTION





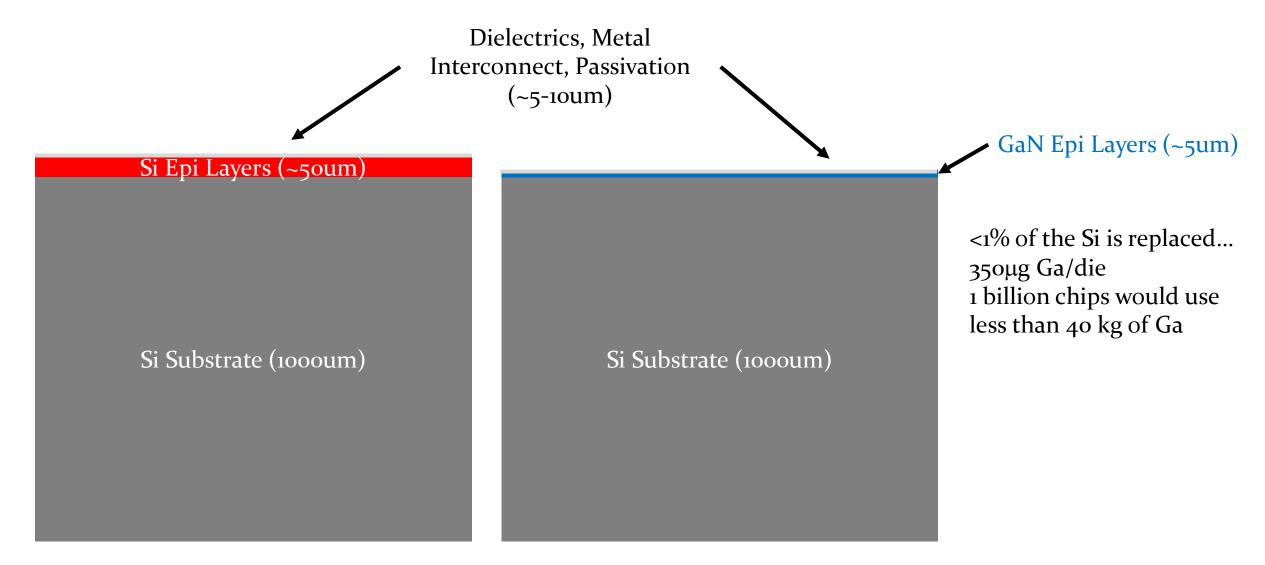
Ga IS A BYPRODUCT OF BAUXITE PROCESSING



Bauxite Deposits

HIGH VOLTAGE Si vs GaN COMPARISON





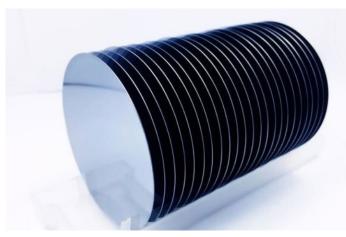
Si High Voltage MOSFET

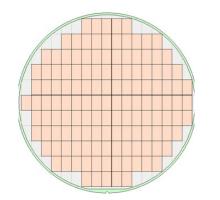
GaN High Voltage HEMT

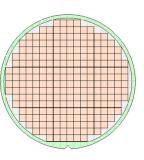
HIGH VOLTAGE Si vs GaN COMPARISON



	Si High Voltage MOSFET	GaN HEMT
Material	Si wafer	Si wafer
Wafer Diameter	8"	6"
Starting Wafer Thickness	500-1000um	1000 um
Finished Wafer Thickness	100-200um	250-300um
Die per wafer (equivalent device)	1	1.7



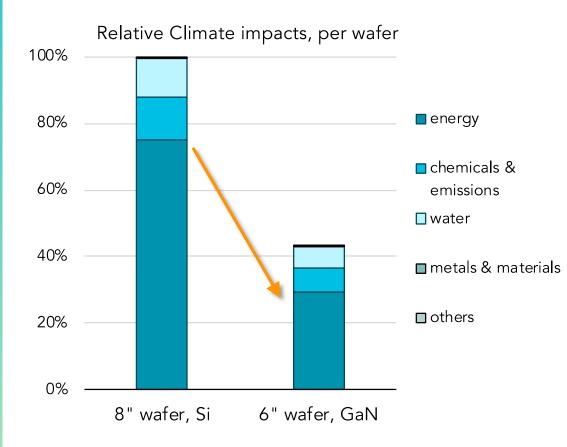




- After GaN epi, GaN technology is similar to existing CMOS processing technology
- Existing (sometimes idle) 6" and 8" fab capacity/infrastructure can be used with small investment



ENERGY DRIVES ENVIRONMENTAL IMPACTS IN FABRICATION



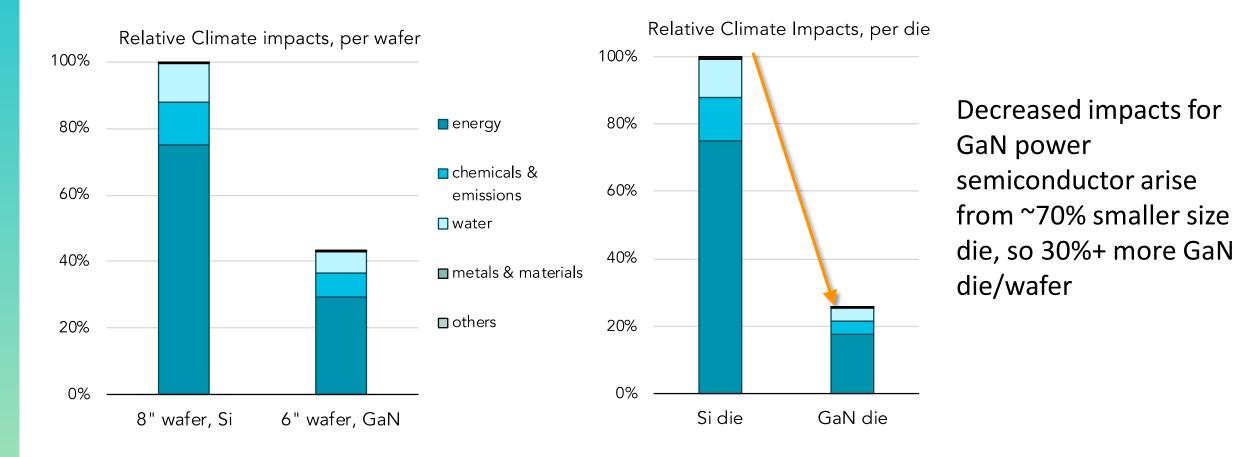
Decreased impacts for GaN power semiconductors arise from:

- Decreased energy needs in fabrication due to fewer furnace and other processes than for conventional Si wafer production
- Decreased material and processing due to significantly smaller epitaxial thickness for GaN typography





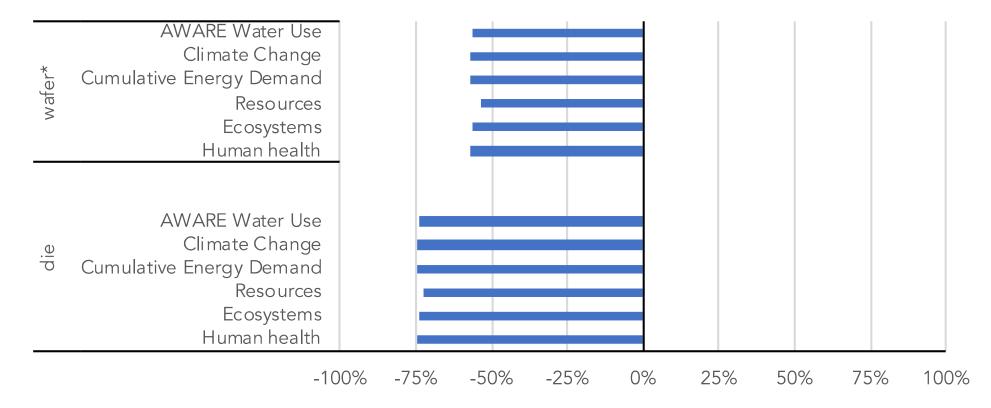
GaN'S SMALL DIE SIZE MEANS MANY MORE DIE PER WAFER





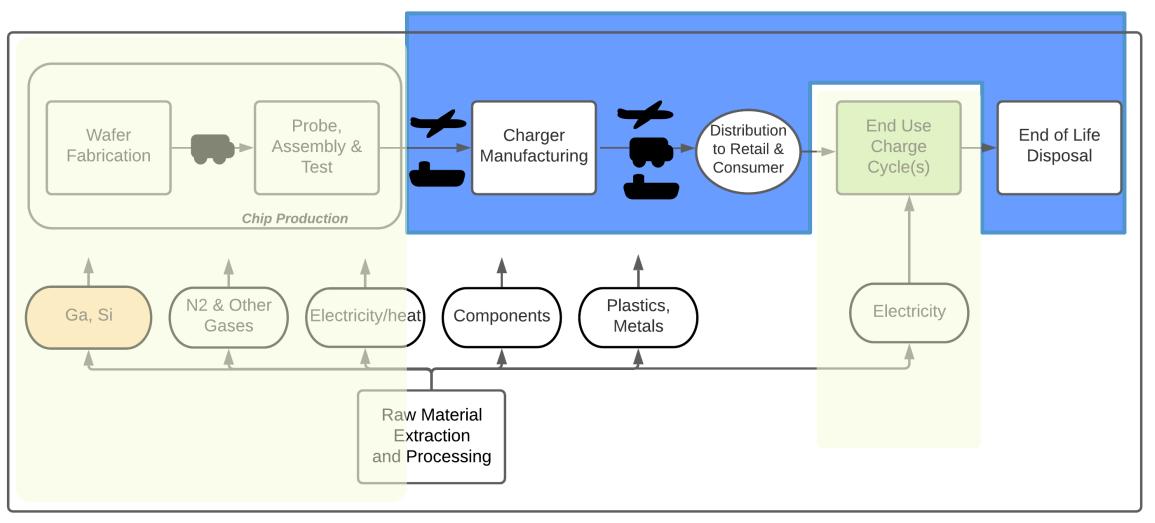
WAFER & DIE IMPACTS FOR GaN RELATIVE TO Si: reduction in all assessed categories

Change in Potential Impact with GaN





CHARGER PRODUCTION, DISTRIBUTION & DISPOSAL

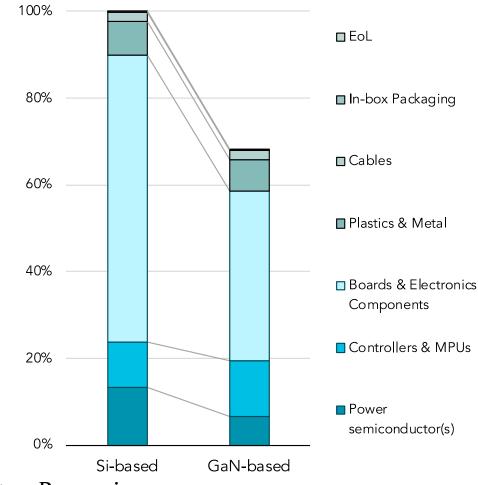


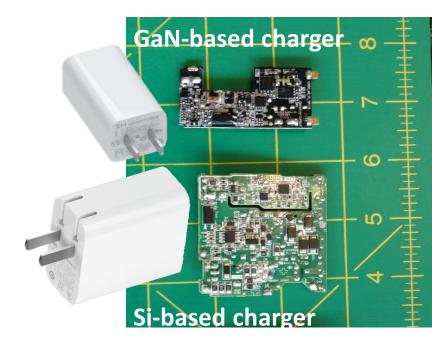




DEMATERIALIZATION: USING THE GAN CHIP DECREASED CHARGER COMPONENTS AND WEIGHTS

Relative Climate Impacts, 65W Charger





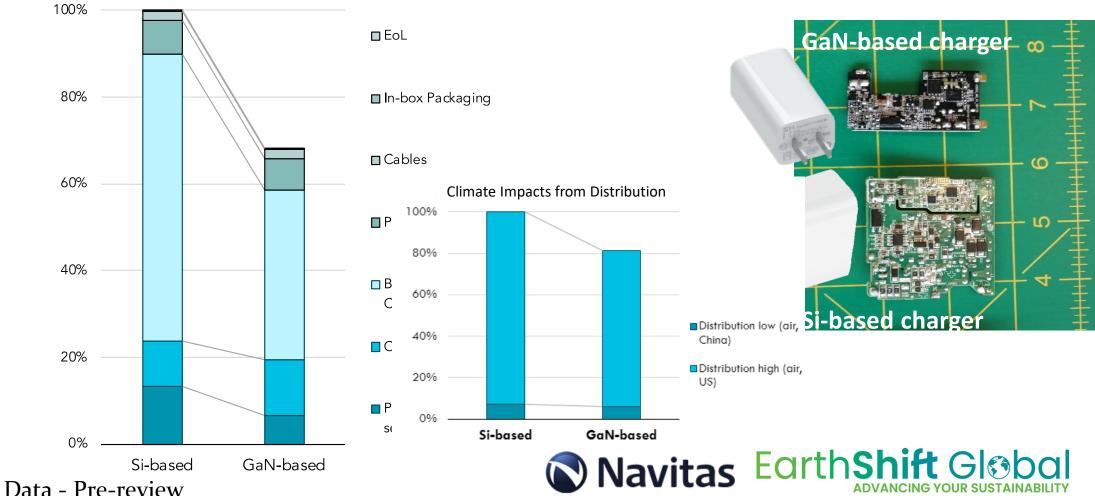


Navitas EarthShift Global

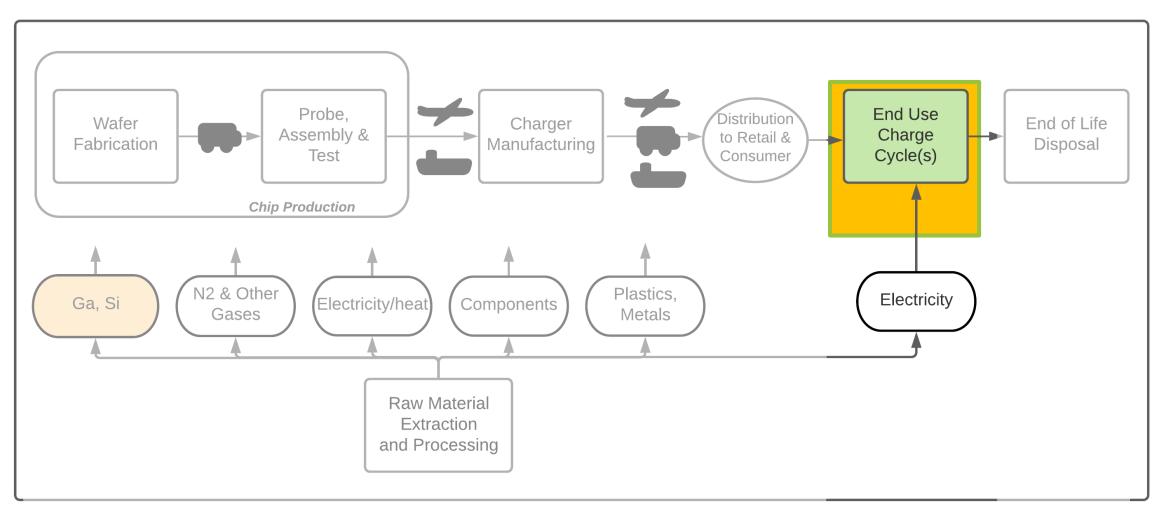


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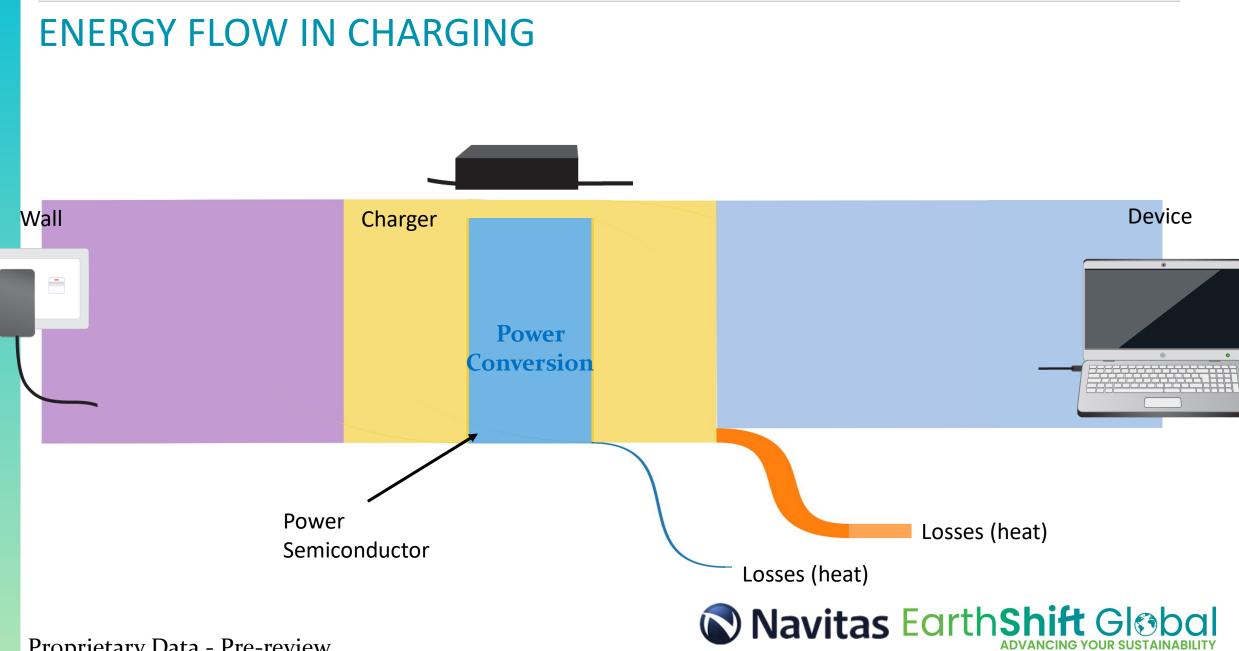
Relative Climate Impacts, 65W Charger



USE PHASE



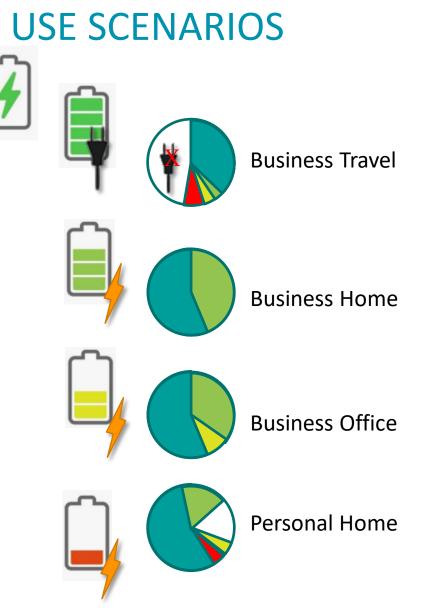




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Wafer Fabrication Chip Production

Units

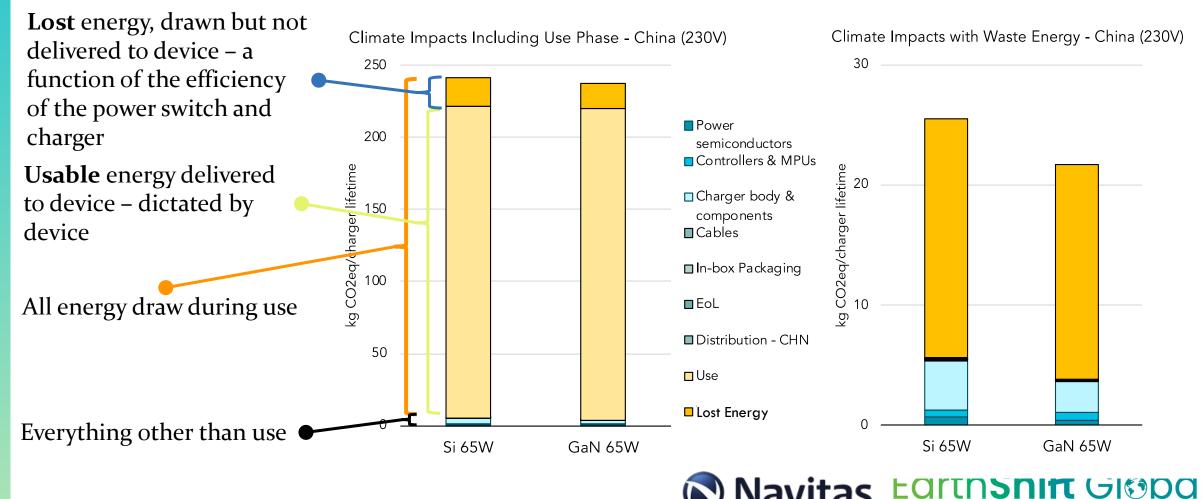


		Chip Production			Ī
Scenario	Business	Business	Business	Personal	Uni
	Travel	Home	Office	Home	
Continuous use					
hours	0	10	8.5	4	hours
% of base power	30%	30%	30%	30%	%
Not connected to charger					
Use on battery only					
hours	11	0.00	1.00	4.00	hours
% of base power	0%	0%	0%	0%	%
"Abandoned" plug					
hours	0	0.00	1.00	4.00	hours
% of base power used, 110/120V (GaN charger)	0.0724%	0.0724%	0.0724%	0.0724%	%
% of base power used, 220/230V (GaN charger)	0.1686%	0.1686%	0.1686%	0.1686%	%
Charge up, active					
hours	1.5			0.5	hours
% of base power delivered	100%			100%	%
hours	0.75		0.25	0.25	hours
% of base power delivered	50%		50%	50%	%
hours	0.75		0.25	0.25	hours
% of base power delivered	30%		30%	30%	%
Charge up, night					
hours	0.5				hours
% of base power delivered	100%				%
hours	0.25				hours
% of base power delivered	50%				%
hours	0.25				hours
% of base power delivered	30%				%
Fully charged, Plugged in, no use					
hours	9	14	14	15	hours
% of base power delivered	15%	15%	15%	15%	%
Total daily hours accounted for	24	24	24	24	
-					

USE IS THE MOST SIGNIFICANT CONTRIBUTOR TO IMPACTS

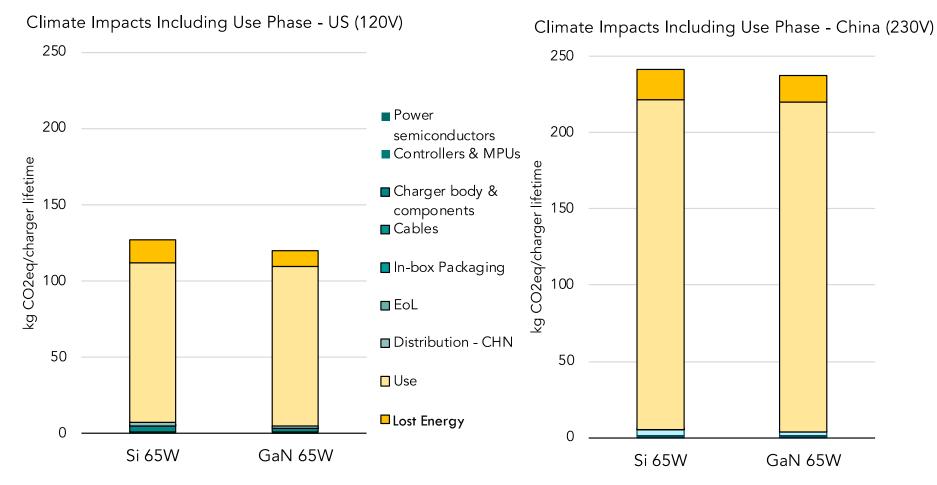
Work Travel Scenario (work untethered, plugged in only to charge)

End Use Charge Cycle(s)





USE PHASE IMPACTS IN DIFFERENT REGIONS

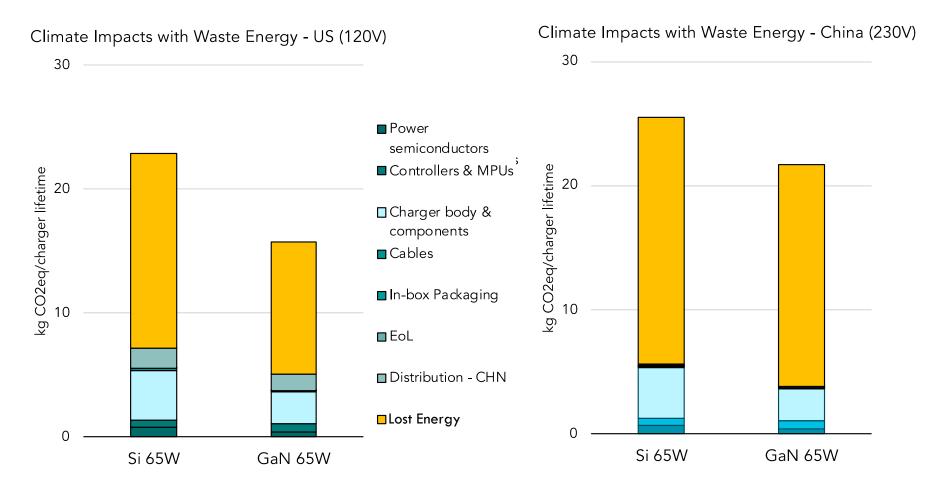


Work Travel Scenario (work untethered, plugged in only to charge)





USE PHASE IMPACTS IN DIFFERENT REGIONS

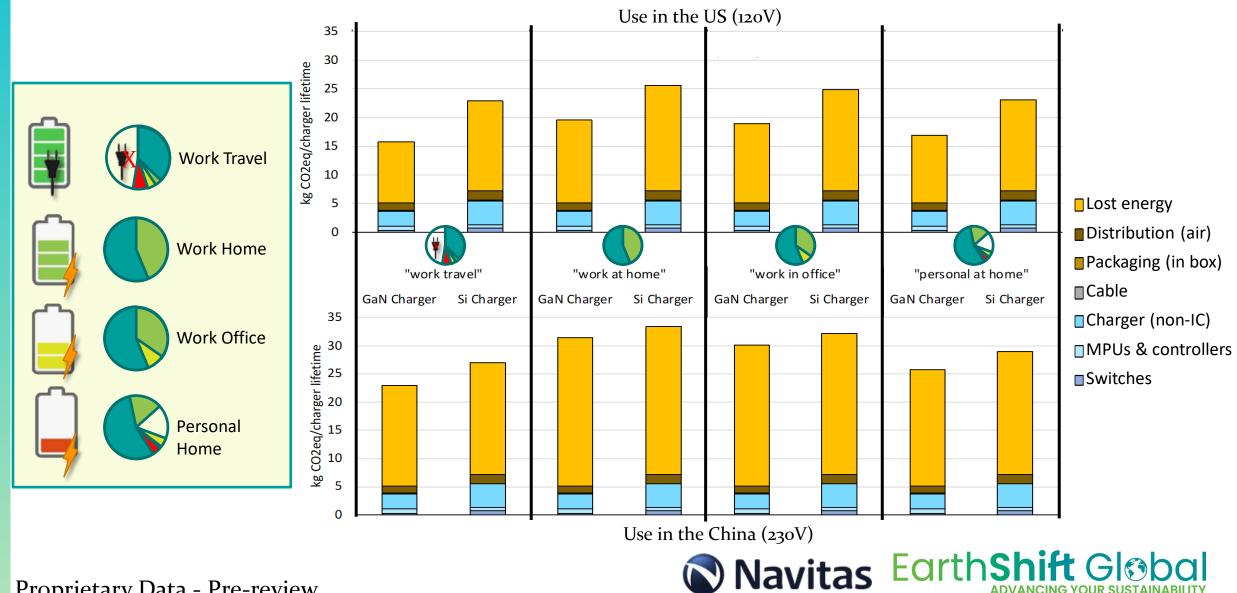


Work Travel Scenario (work untethered, plugged in only to charge)





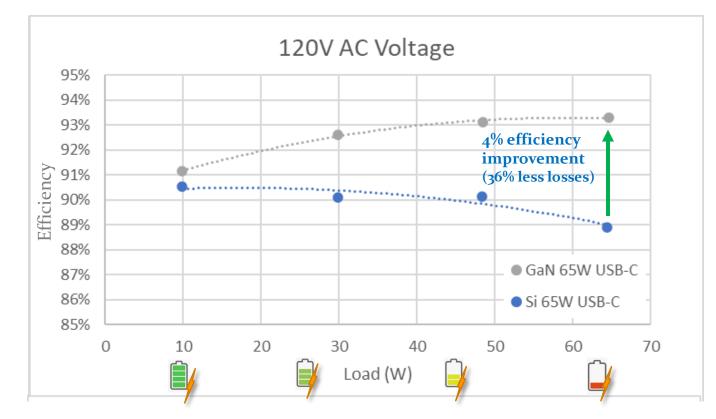
OTHER USE PATTERNS LOOK A BIT DIFFERENT



LCA LEARNINGS – DESIGN CONSIDERATIONS



- Worst case power dissipation is at full load (65W) condition
 - Defines adapter size → Key factor in manufacturing impacts and dematerialization opportunities
- The Use-cases for this study show tradeoffs for Use-Phase Impacts
 - Total energy use across various use-cases: 70% heavy load / 30% light load
 - Full load efficiency is more important for use cases that include more charging and less plugged-in non-use



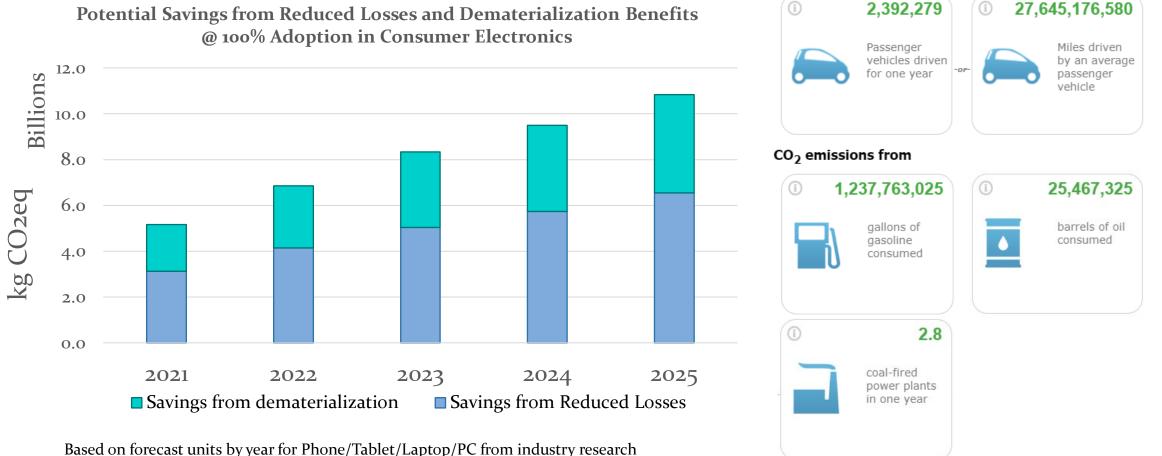
- Light load efficiency becomes a larger factor for applications normally plugged in with light/moderate use \rightarrow needs optimization across the power range
- Geography impacts Use-Phase impacts
 - Most adapters are targeted for global use so must be optimized for both AC voltage conditions

CURRENT FINDINGS & NEXT STEPS

- The results from the ongoing study
 - Are validating that the manufacturing impacts are on the order of the energy savings, so that both use and 'dematerialization' are relevant and need to be included in the the design and vision
 - Are demonstrating that full use cases on the end product are key to understanding how to optimize in order to capture the full benefit of the new technology
 - Have so far found no unforeseen consequences or tradeoffs
- Data gaps and data quality factors for key electronic components are unexpectedly challenging primary data for fabrication is severely lacking, and literature data is a lot older than expected – uncertainty is high.
- The current study is examining only one of several significant applications for the GaN technology. Future work will look at additional consumer charging applications as well as industrial scale uses.



HOW SIGNIFICANT IS THE POTENTIAL BENEFIT FROM ADOPTION IN **CONSUMER ELECTRONICS?**



Greenhouse gas emissions from

EarthShift Global

ADVANCING YOUR SUSTAINARII

Based on forecast units by year for Phone/Tablet/Laptop/PC from industry research

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Thank you for your time. We're happy to answer questions, now or later:

Caroline Taylor, PhD, caroline@earthshiftglobal.com

Anthony Schiro, anthony.schiro@navitassemi.com

• USA • Canada • Colombia •

• +1 (207) 608-6228 • www.earthshiftglobal.com •





SUPPLEMENTAL SLIDES



LAPTOP & CHARGING USE PATTERNS

